Sushant Mittal

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/199971/publications.pdf

Version: 2024-02-01

23	132	7	8
papers	citations	h-index	g-index

1307594 1588992

23	23	23	106
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Via Size Optimization for Optimum Circuit Performance at 3 nm node. , 2020, , .		1
2	Impact of MOL/BEOL Air-Spacer on Parasitic Capacitance and Circuit Performance at 3 nm Node. , 2019, , .		9
3	Highly-Doped Through-Contact Silicon Epi Design at 3 nm node. , 2019, , .		1
4	Scaling NC-FinFET to Sub-3 nm Nodes. , 2018, , .		0
5	Selective Fin Trimming after Dummy Gate Removal as the Local Fin Width Scaling Approach for N5 and Beyond. , 2018, , .		2
6	The First Compact Model to Determine <inline-formula> <tex-math notation="LaTeX">V_{T} </tex-math> </inline-formula> Distribution for DG-FinFET Due to LER. IEEE Transactions on Electron Devices, 2018, 65, 4772-4779.	3.0	8
7	Analytical modeling of metal gate granularity based threshold voltage variability in NWFET. Solid-State Electronics, 2018, 147, 26-34.	1.4	5
8	An Analytical Model to Estimate ${V}_{T}$ Distribution of Partially Correlated Fin Edges in FinFETs Due to Fin-Edge Roughness. IEEE Transactions on Electron Devices, 2017, 64, 1708-1715.	3.0	9
9	Analytical Model to Estimate FinFETâ€™s ${ext I}_{ext {ON}}$, ${ext I}_{ext{OFF}}$, SS, and ${m V}_{T}$ Distribution Due to FER. IEEE Transactions on Electron Devices, 2017, 64, 3489-3493.	3.0	13
10	Analytical Estimation of Threshold Voltage Variability by Metal Gate Granularity in FinFET. IEEE Transactions on Electron Devices, 2017, 64, 3071-3076.	3.0	27
11	An Analytical Model to Estimate FinFET's V_TDistribution Due to Fin-Edge Roughness. IEEE Transactions on Electron Devices, 2016, 63, 1352-1358.	3.0	17
12	Statistical Variability Analysis of SRAM Cell for Emerging Transistor Technologies. IEEE Transactions on Electron Devices, 2016, 63, 3514-3520.	3.0	7
13	Analytical modeling of metal gate granularity induced V<inf>t</inf> variability in NWFETs. , 2016, , .		2
14	A Bulk Planar SiGe Quantum-Well Based ZRAM with Low Vt Variability. , 2015, , .		1
15	FinFET scaling rule based On variability considerations. , 2015, , .		4
16	A FinFET LER V<inf>T</inf> variability estimation scheme with 300× efficiency improvement. , 2014, , .		3
17	Cryogenic implantation for source/drain junctions in Ge p-channel (Fin)FETs. , 2014, , .		0
18	Epitaxial rare earth oxide (EOx) FinFET: A variability-resistant Ge FinFET architecture with multi V<inf>T</inf>. , 2014, , .		2

#	Article	IF	Citations
19	Epitaxially Defined FinFET: Variability Resistant and High-Performance Technology. IEEE Transactions on Electron Devices, 2014, 61, 2711-2718.	3.0	11
20	Dopant deactivation: A new challenge in sub-20nm scaled FinFETs. , 2014, , .		1
21	Epi defined (ED) FinFET: An alternate device architecture for high mobility Ge channel integration in PMOSFET. , 2013, , .		4
22	Epi Defined (ED) FinFET with dynamic threshold: Reduced V<inf>T</inf> variability, enhanced performance, and a novel Multiple V<inf>T</inf>. , 2013, , .		0
23	Epitaxialy defined (ED) FinFET: to reduce V<inf>T</inf> variability and enable multiple V<inf>T</inf>. , 2012, , .		5